FAIRCHILD SEMICONDUCTOR®

February 2007

# FDMS2572
# N-Channel UltraFET Trench® MOSFET
## 150V, 27A, 47mΩ

## Features

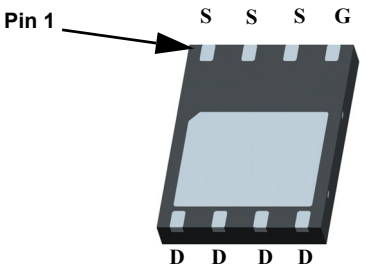
- Max $r_{DS(on)}$ = 47mΩ at $V_{GS}$ = 10V, $I_D$ = 4.5A
- Max $r_{DS(on)}$ = 53mΩ at $V_{GS}$ = 6V, $I_D$ = 4.5A
- Low Miller Charge
- Optimized efficiency at high frequencies
- UIS Capability (Single pulse and Repetitive pulse)
- RoHS Compliant

## General Description

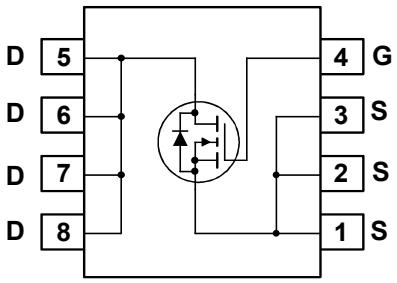
UltraFET devices combine characteristics that enable benchmark efficiency in power conversion applications. Optimized for $r_{DS(on)}$, low ESR, low total and Miller gate charge, these devices are ideal for high frequency DC to DC converters.

## Application

- Distributed Power Architectures and VRMs
- Primary Switch for 24V and 48V Systems
- High Voltage Synchronous Rectifier




Power 56 (Bottom view)




## MOSFET Maximum Ratings $T_A$ = 25°C unless otherwise noted

| Symbol | Parameter | | | Ratings | Units |
|---|---|---|---|---|---|
| $V_{DS}$ | Drain to Source Voltage | | | 150 | V |
| $V_{GS}$ | Gate to Source Voltage | | | ±20 | V |
| $I_D$ | Drain Current -Continuous (Package limited) | $T_C$ = 25°C | | 27 | A |
| | -Continuous (Silicon limited) | $T_C$ = 25°C | | 27 | |
| | -Continuous | $T_A$ = 25°C | (Note 1a) | 4.5 | |
| | -Pulsed | | | 30 | |
| $P_D$ | Power Dissipation | $T_C$ = 25°C | | 78 | W |
| | Power Dissipation | $T_A$ = 25°C | (Note 1a) | 2.5 | |
| $T_J$, $T_{STG}$ | Operating and Storage Junction Temperature Range | | | -55 to +150 | °C |

## Thermal Characteristics

| | | | |
|---|---|---|---|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case | 1.6 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient (Note 1a) | 50 | |

## Package Marking and Ordering Information

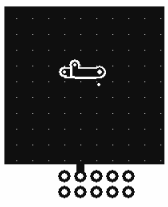
| Device Marking | Device | Package | Reel Size | Tape Width | Quantity |
|---|---|---|---|---|---|
| FDMS2572 | FDMS2572 | Power 56 | 13” | 12mm | 3000 units |

## Electrical Characteristics $T_J$ = 25°C unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|---|---|---|---|---|---|---|
| **Off Characteristics** | | | | | | |
| $BV_{DSS}$ | Drain to Source Breakdown Voltage | $I_D$ = 250μA, $V_{GS}$ = 0V | 150 | | | V |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D$ = 250μA, referenced to 25°C | | 180 | | mV/°C |
| $I_{DSS}$ | Zero Gate Voltage Drain Current | $V_{DS}$ = 120V, $V_{GS}$ = 0V | | | 1 | μA |
| $I_{GSS}$ | Gate to Source Leakage Current | $V_{GS}$ = ±20V, $V_{DS}$ = 0V | | | ±100 | nA |
| **On Characteristics** (Note 2) | | | | | | |
| $V_{GS(th)}$ | Gate to Source Threshold Voltage | $V_{GS}$ = $V_{DS}$, $I_D$ = 250μA | 2 | 3 | 4 | V |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate to Source Threshold Voltage Temperature Coefficient | $I_D$ = 250μA, referenced to 25°C | | -9.8 | | mV/°C |
| $r_{DS(on)}$ | Drain to Source On Resistance | $V_{GS}$ = 10V, $I_D$ = 4.5A | | 36 | 47 | mΩ |
| | | $V_{GS}$ = 6V, $I_D$ = 4.5A | | 39 | 53 | |
| | | $V_{GS}$ = 10V, $I_D$ = 4.5A, $T_J$ = 125°C | | 69 | 103 | |
| $g_{FS}$ | Forward Transconductance | $V_{DS}$ = 10V, $I_D$ = 4.5A | | 14 | | S |
| **Dynamic Characteristics** | | | | | | |
| $C_{iss}$ | Input Capacitance | $V_{DS}$ = 75V, $V_{GS}$ = 0V, f = 1MHz | | 1960 | 2610 | pF |
| $C_{oss}$ | Output Capacitance | | | 130 | 175 | pF |
| $C_{rss}$ | Reverse Transfer Capacitance | | | 30 | 45 | pF |
| $R_g$ | Gate Resistance | f = 1MHz | | 1.3 | | Ω |
| **Switching Characteristics** | | | | | | |
| $t_{d(on)}$ | Turn-On Delay Time | $V_{DD}$ = 75V, $I_D$ = 1.0A, $V_{GS}$ = 10V, $R_{GEN}$ = 6Ω | | 11 | 20 | ns |
| $t_r$ | Rise Time | | | 8 | 16 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time | | | 38 | 61 | ns |
| $t_f$ | Fall Time | | | 31 | 50 | ns |
| $Q_{g(TOT)}$ | Total Gate Charge at 10V | $V_{GS}$ = 0V to 10V, $V_{DD}$ = 75V, $I_D$ = 4.5A | | 31 | 43 | nC |
| $Q_{gs}$ | Gate to Source Gate Charge | | | 9 | | nC |
| $Q_{gd}$ | Gate to Drain “Miller” Charge | | | 7 | | nC |
| **Drain-Source Diode Characteristics** | | | | | | |
| $V_{SD}$ | Source to Drain Diode Forward Voltage | $V_{GS}$ = 0V, $I_S$ = 2.2A (Note 2) | | 0.7 | 1.0 | V |
| $t_{rr}$ | Reverse Recovery Time | $I_F$ = 4.5A, di/dt = 100A/μs | | 67 | 101 | ns |
| $Q_{rr}$ | Reverse Recovery Charge | | | 130 | 195 | nC |

**Notes:**

**1:** $R_{\theta JA}$ is determined with the device mounted on a 1in$^2$ pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a.50°C/W when mounted on a 1 in$^2$ pad of 2 oz copper

b. 125°C/W when mounted on a minimum pad of 2 oz copper

**2:** Pulse Test: Pulse Width < 300μs, Duty cycle < 2.0%.

## Typical Characteristics $T_J$ = 25°C unless otherwise noted

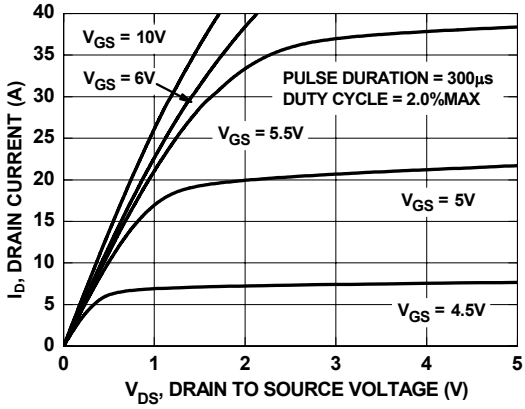



**Figure 1. On-Region Characteristics**

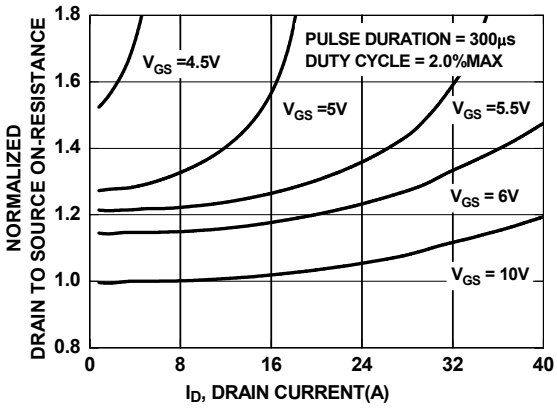



**Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage**

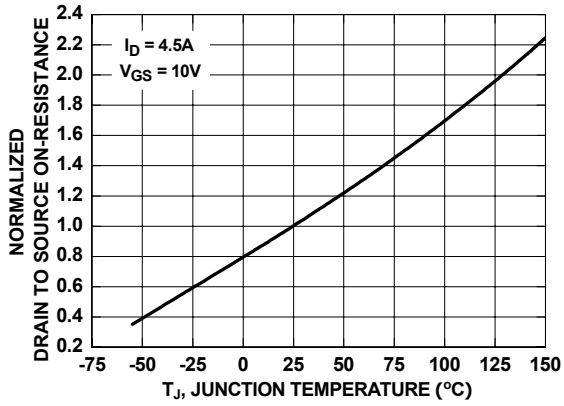



**Figure 3. Normalized On-Resistance vs Junction Temperature**

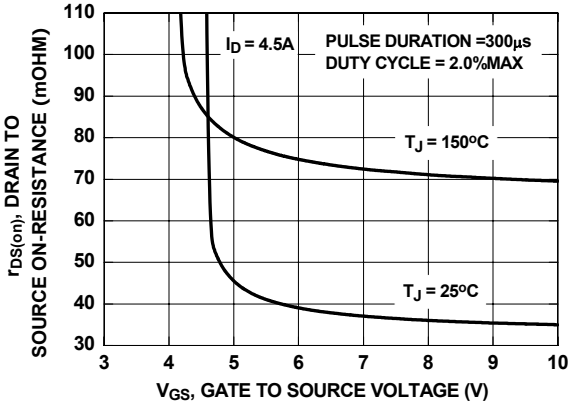



**Figure 4. On-Resistance vs Gate to Source Voltage**

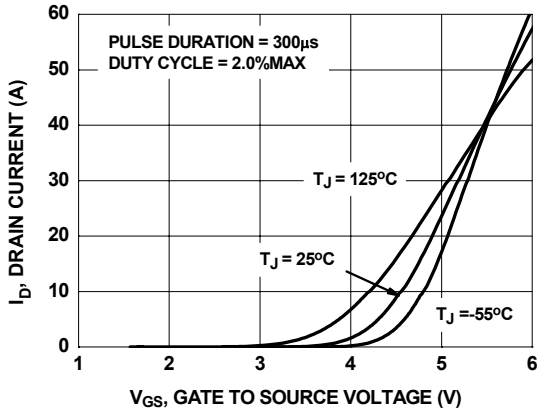



**Figure 5. Transfer Characteristics**

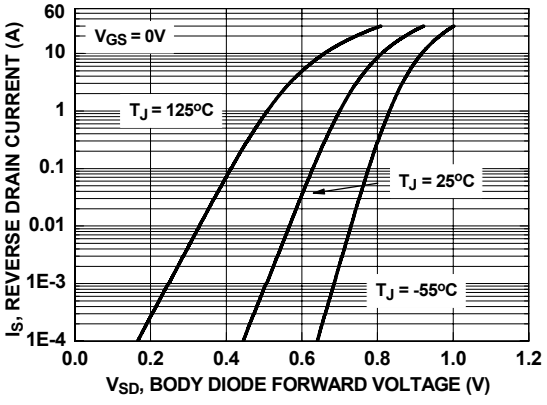



**Figure 6. Source to Drain Diode Forward Voltage vs Source Current**

## Typical Characteristics $T_J$ = 25°C unless otherwise noted

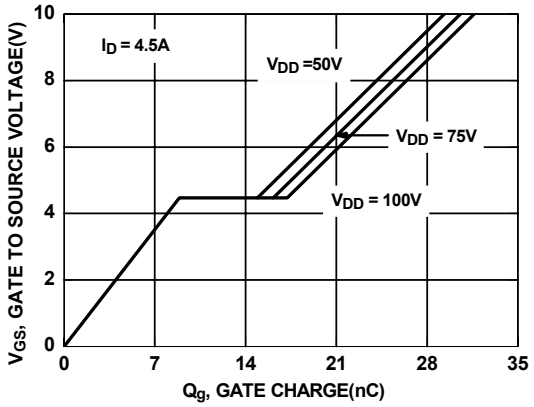



**Figure 7. Gate Charge Characteristics**

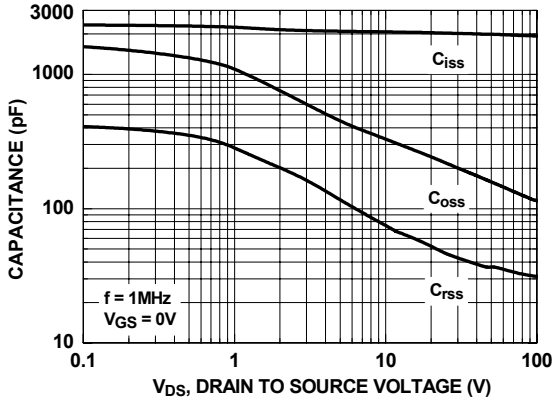



**Figure 8. Capacitance vs Drain to Source Voltage**

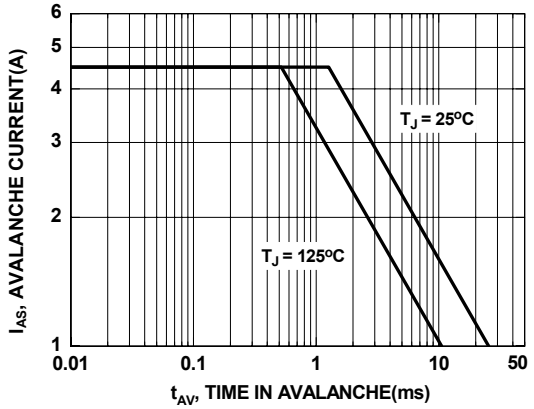



**Figure 9. Unclamped Inductive Switching Capability**

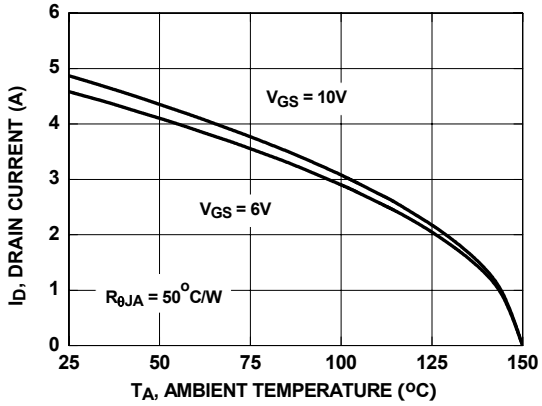



**Figure 10. Maximum Continuous Drain Current vs Ambient Temperature**

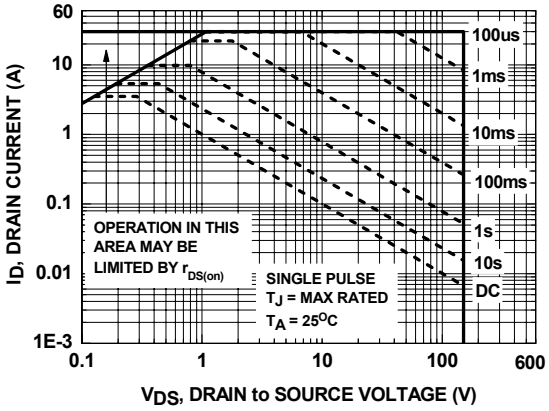



**Figure 11. Forward Bias Safe Operating Area**

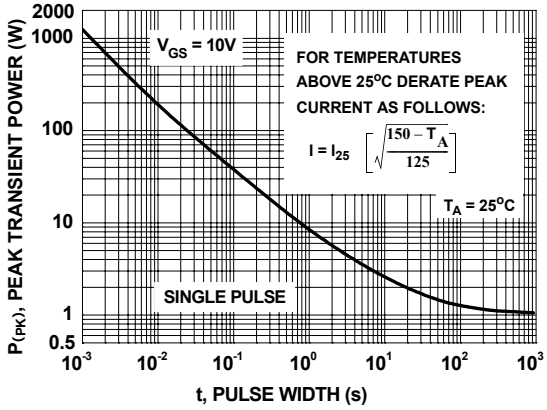



**Figure 12. Single Pulse Maximum Power Dissipation**

## Typical Characteristics $T_J$ = 25°C unless otherwise noted

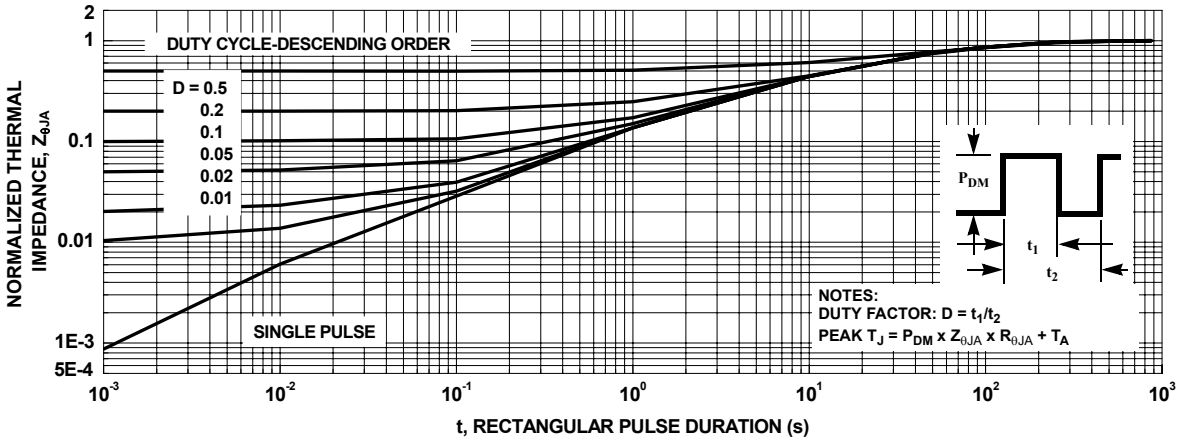
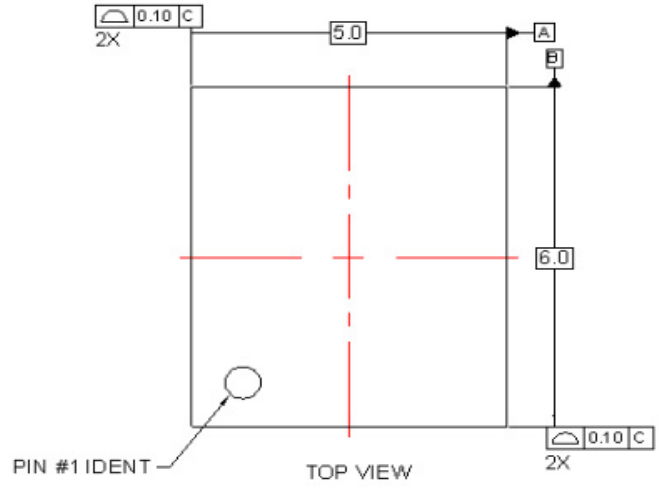
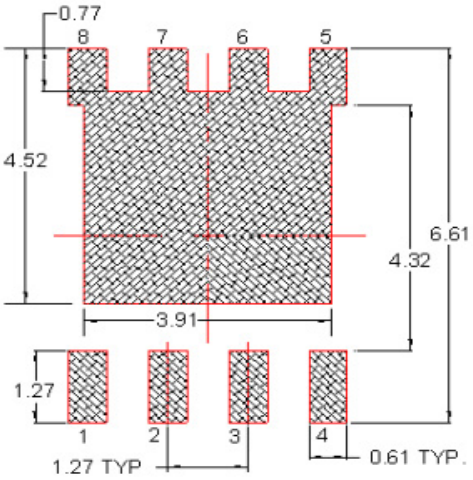



**Figure 13. Transient Thermal Response Curve**

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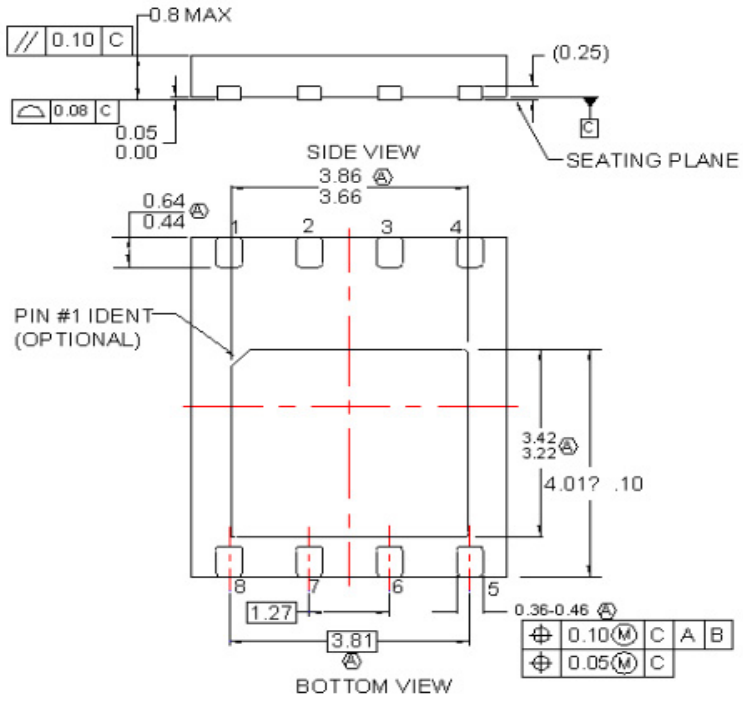


NOTES:

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